



HUF76629D3ST_F085

N-Channel Logic Level UltraFET[®] Power MOSFET

100V, 20A, 52mΩ

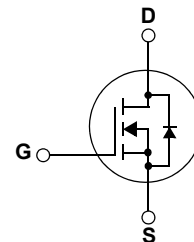
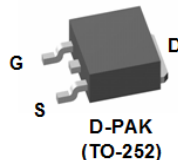
April 2013

Features

- Typ $r_{DS(on)}$ = 41mΩ at V_{GS} = 10V, I_D = 20A
- Typ $Q_{g(tot)}$ = 39nC at V_{GS} = 10V, I_D = 20A
- UIS Capability
- RoHS Compliant
- Qualified to AEC Q101

Applications

- Automotive Engine Control
- Powertrain Management
- Solenoid and Motor Drivers
- Distributed Power Architectures and VRM
- Primary Switch for 12V Systems



MOSFET Maximum Ratings $T_J = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain to Source Voltage	100	V
V_{GS}	Gate to Source Voltage	±16	V
I_D	Drain Current - Continuous ($V_{GS}=10$) (Note 1)	20	A
	Pulsed Drain Current	See Figure4	
E_{AS}	Single Pulse Avalanche Energy (Note 2)	231	mJ
P_D	Power Dissipation	150	W
	Derate above 25°C	1	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature	-55 to + 175	$^\circ\text{C}$
$R_{\theta JC}$	Thermal Resistance Junction to Case	1	$^\circ\text{C/W}$
$R_{\theta JA}$	Maximum Thermal Resistance Junction to Ambient (Note 3)	52	$^\circ\text{C/W}$

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
HUF76629D3ST	HUF76629D3ST_F085	D-PAK(TO-252)	13"	12mm	2500 units

Notes:

- 1: Current is limited by bondwire configuration.
- 2: Starting $T_J = 25^\circ\text{C}$, $L = 1.8\text{mH}$, $I_{AS} = 16\text{A}$, $V_{DD} = 100\text{V}$ during inductor charging and $V_{DD} = 0\text{V}$ during time in avalanche
- 3: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design. The maximum rating presented here is based on mounting on a 1 in² pad of 2oz copper.

HUF76629D3ST_F085 N-Channel Logic Level UltraFET[®] Power MOSFET

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
--------	-----------	-----------------	-----	-----	-----	-------

Off Characteristics

$B_{V_{DS}}$	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	100	-	-	V
I_{DSS}	Drain to Source Leakage Current	$V_{DS} = 100\text{V}$, $T_J = 25^\circ\text{C}$ $V_{GS} = 0\text{V}$, $T_J = 175^\circ\text{C}$ (Note 4)	-	-	1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 16\text{V}$	-	-	± 100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\mu\text{A}$	1.0	1.6	3.0	V
$r_{DS(on)}$	Drain to Source On Resistance	$I_D = 20\text{A}$, $T_J = 25^\circ\text{C}$	-	41	52	$\text{m}\Omega$
		$V_{GS} = 10\text{V}$, $T_J = 175^\circ\text{C}$ (Note 4)	-	102	128	$\text{m}\Omega$
		$I_D = 20\text{A}$, $T_J = 25^\circ\text{C}$	-	47	55	$\text{m}\Omega$
		$V_{GS} = 4.5\text{V}$, $T_J = 175^\circ\text{C}$ (Note 4)	-	115	135	$\text{m}\Omega$

Dynamic Characteristics

C _i ss	Input Capacitance	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz		-	1280	-	pF
C _{oss}	Output Capacitance			-	214	-	pF
C _r ss	Reverse Transfer Capacitance			-	33	-	pF
R _g	Gate Resistance	f = 1MHz		-	2.5	-	Ω
Q _g (ToT)	Total Gate Charge	V _{GS} = 0 to 10V	V _{DD} = 50V I _D = 20A	-	39	43	nC
Q _g (th)	Threshold Gate Charge	V _{GS} = 0 to 2V		-	2.3	3	nC
Q _{gs}	Gate to Source Gate Charge			-	3.5	-	nC
Q _{gd}	Gate to Drain “Miller” Charge			-	11	-	nC

Switching Characteristics

t_{on}	Turn-On Time	$V_{DD} = 50\text{V}$, $I_D = 20\text{A}$, $V_{GS} = 10\text{V}$, $R_{GEN} = 8.2\Omega$	-	-	27	ns
$t_{d(on)}$	Turn-On Delay Time		-	7	-	ns
t_r	Rise Time		-	12	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	38	-	ns
t_f	Fall Time		-	5	-	ns
t_{off}	Turn-Off Time		-	-	47	ns

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Voltage	$I_{SD} = 20\text{A}$, $V_{GS} = 0\text{V}$	-	-	1.25	V
		$I_{SD} = 10\text{A}$, $V_{GS} = 0\text{V}$	-	-	1.0	V
T_{rr}	Reverse Recovery Time	$I_F = 20\text{A}$, $di_{SD}/dt = 100\text{A}/\mu\text{s}$, $V_{DD} = 80\text{V}$	-	77	99	ns
Q_{rr}	Reverse Recovery Charge		-	221	305	nC

Notes:

4: The maximum value is specified by design at $T_J = 175^\circ\text{C}$. Product is not tested to this condition in production.

Typical Characteristics

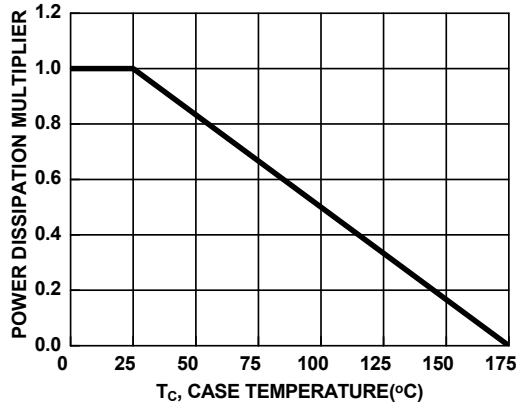


Figure 1. Normalized Power Dissipation vs Case Temperature

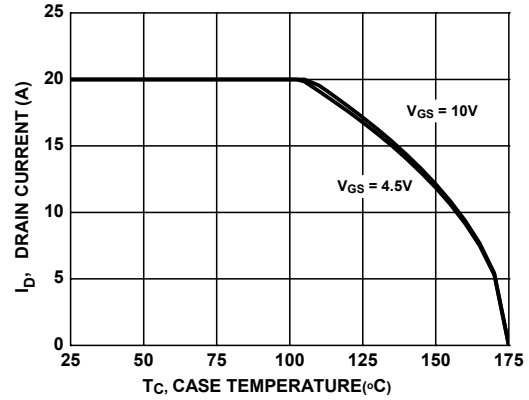


Figure 2. Maximum Continuous Drain Current vs Case Temperature

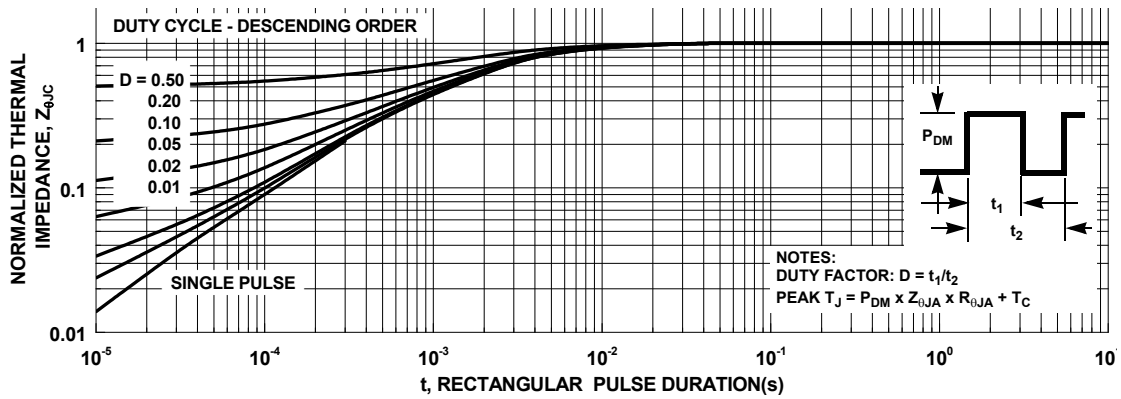


Figure 3. Normalized Maximum Transient Thermal Impedance

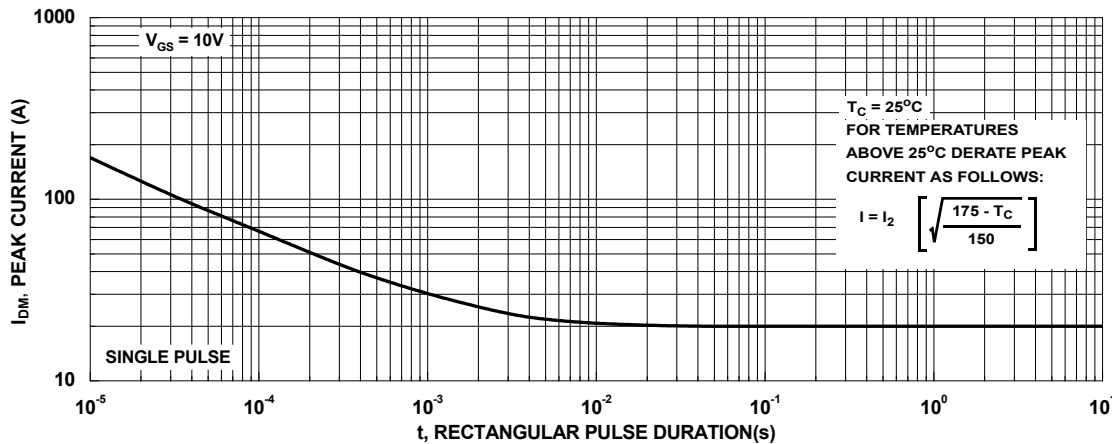


Figure 4. Peak Current Capability

Typical Characteristics

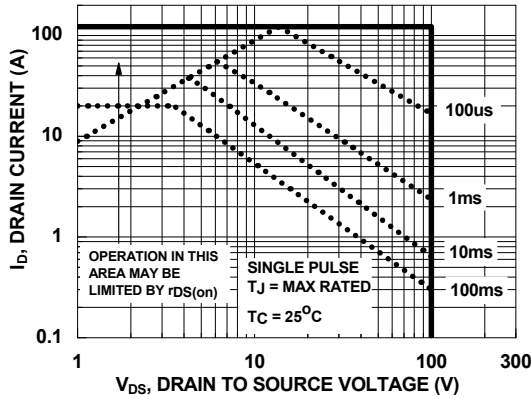
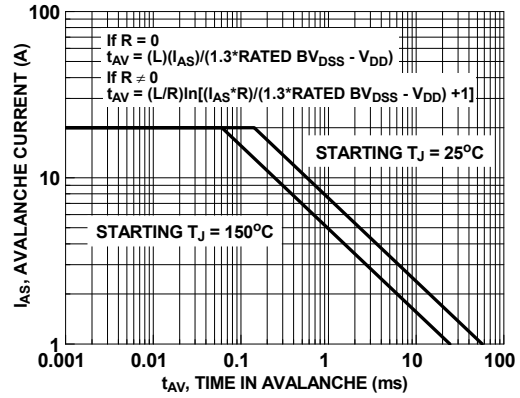


Figure 5. Forward Bias Safe Operating Area



NOTE: Refer to Fairchild Application Notes AN7514 and AN7515

Figure 6. Unclamped Inductive Switching Capability

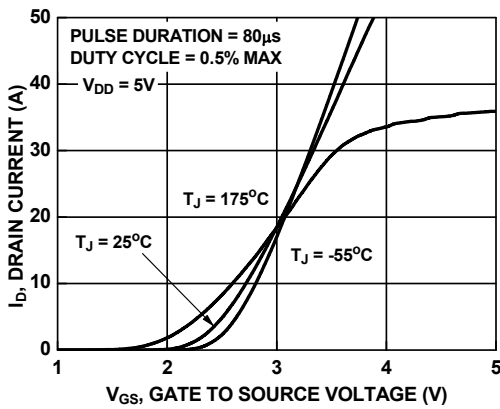


Figure 7. Transfer Characteristics

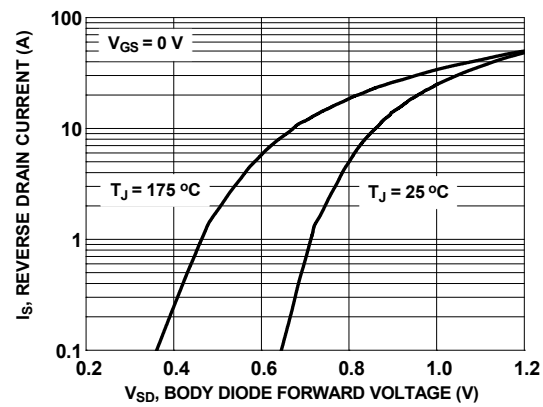


Figure 8. Forward Diode Characteristics

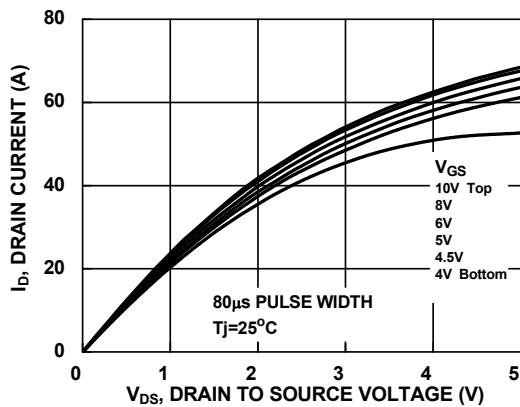


Figure 9. Saturation Characteristics

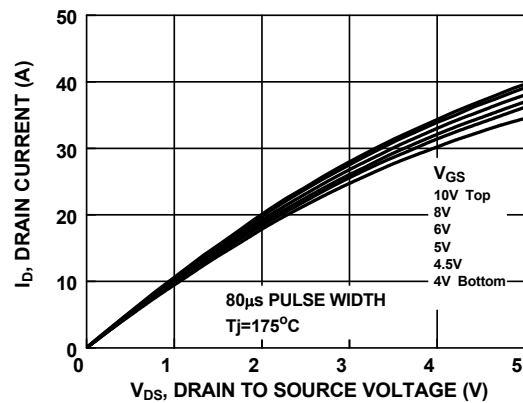


Figure 10. Saturation Characteristics

Typical Characteristics

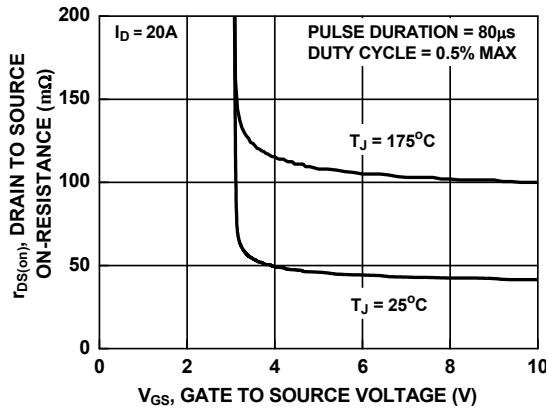


Figure 11. $R_{ds(on)}$ vs Gate Voltage

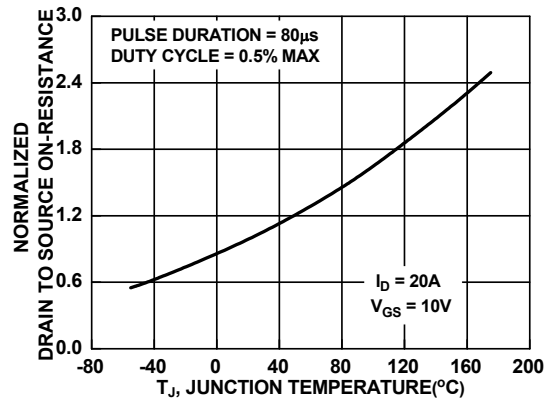


Figure 12. Normalized $R_{ds(on)}$ vs Junction Temperature

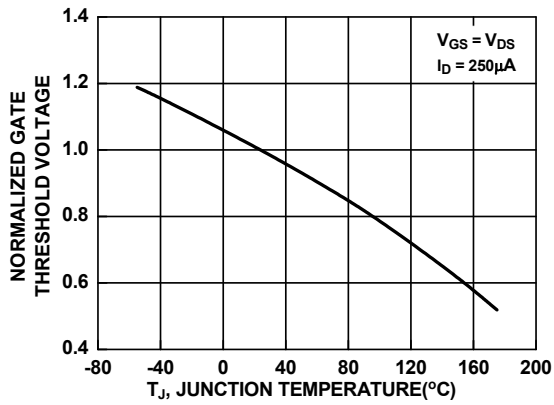


Figure 13. Normalized Gate Threshold Voltage vs Temperature

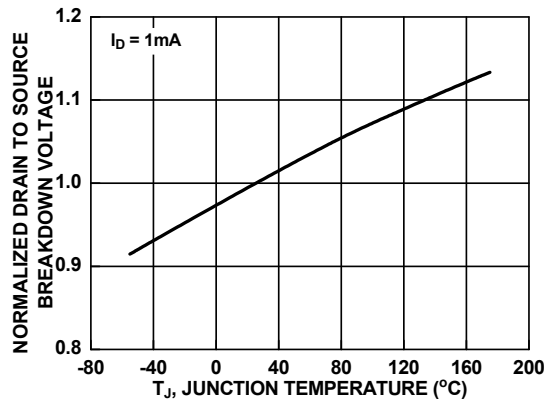


Figure 14. Normalized Drain to Source Breakdown Voltage vs Junction Temperature

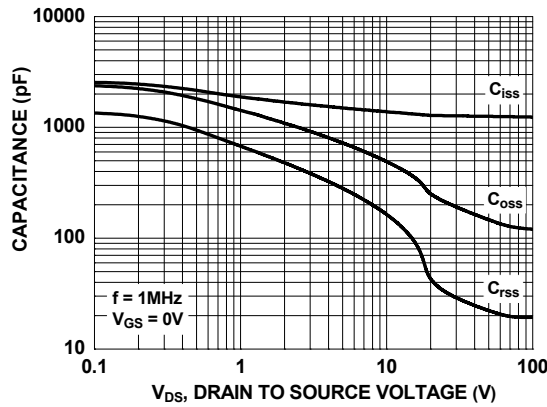


Figure 15. Capacitance vs Drain to Source Voltage

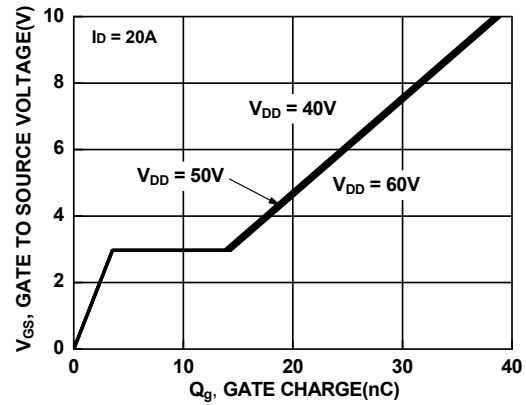


Figure 16. Gate Charge vs Gate to Source Voltage



TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

2Cool™	FPS™	PowerTrench®	Sync-Lock™
AccuPower™	F-PFST™	PowerXS™	SYSTEM GENERAL®*
AX-CAP®*	FRFET®	Programmable Active Droop™	TinyBoost™
BitSiC™	Global Power Resource SM	QFET®	TinyBuck™
Build it Now™	Green Bridge™	QS™	TinyCalc™
CorePLUS™	Green FPS™	Quiet Series™	TinyLogic®
CorePOWER™	Green FPS™ e-Series™	RapidConfigure™	TINYOPTO™
CROSSVOLT™	Gmax™	TM	TinyPower™
CTL™	GTO™	Saving our world, 1mW/W/kW at a time™	TinyPWM™
Current Transfer Logic™	IntelliMAX™	SignalWise™	TinyWire™
DEUXPEED®	ISOPLANAR™	SmartMax™	TranSiC®
Dual Cool™	Marking Small Speakers Sound Louder and Better™	SMART START™	TriFault Detect™
EcoSPARK®	MegaBuck™	Solutions for Your Success™	TRUECURRENT®*
EfficientMax™	MICROCOUPLER™	SPM®	μSerDes™
ESBC™	MicroFET™	STEALTH™	UHC®
	MicroPak™	SuperFET®	Ultra FRFET™
Fairchild®	MicroPak2™	SuperSOT™-3	UniFET™
Fairchild Semiconductor®	MillerDrive™	SuperSOT™-6	VCX™
FACT Quiet Series™	MotionMax™	SuperSOT™-8	VisualMax™
FACT®	mWSaver™	SupreMOS®	VoltagePlus™
FAST®	OptoHiT™	SyncFET™	XS™
FastvCore™	OPTOLOGIC®		
FETBench™	OPTOPLANAR®		

*Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used here in:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. 164



**Стандарт
Электрон
Связь**

Мы молодая и активно развивающаяся компания в области поставок электронных компонентов. Мы поставляем электронные компоненты отечественного и импортного производства напрямую от производителей и с крупнейших складов мира.

Благодаря сотрудничеству с мировыми поставщиками мы осуществляем комплексные и плановые поставки широчайшего спектра электронных компонентов.

Собственная эффективная логистика и склад в обеспечивает надежную поставку продукции в точно указанные сроки по всей России.

Мы осуществляем техническую поддержку нашим клиентам и предпродажную проверку качества продукции. На все поставляемые продукты мы предоставляем гарантию .

Осуществляем поставки продукции под контролем ВП МО РФ на предприятия военно-промышленного комплекса России , а также работаем в рамках 275 ФЗ с открытием отдельных счетов в уполномоченном банке. Система менеджмента качества компании соответствует требованиям ГОСТ ISO 9001.

Минимальные сроки поставки, гибкие цены, неограниченный ассортимент и индивидуальный подход к клиентам являются основой для выстраивания долгосрочного и эффективного сотрудничества с предприятиями радиоэлектронной промышленности, предприятиями ВПК и научно-исследовательскими институтами России.

С нами вы становитесь еще успешнее!

Наши контакты:

Телефон: +7 812 627 14 35

Электронная почта: sales@st-electron.ru

Адрес: 198099, Санкт-Петербург,
Промышленная ул, дом № 19, литера Н,
помещение 100-Н Офис 331